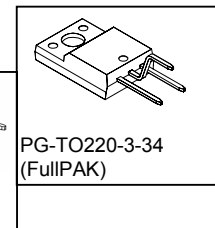
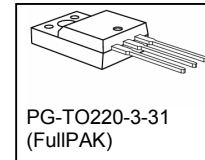
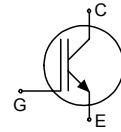


## HighSpeed 2-Technology

- Designed for:**
  - TV – Horizontal Line Deflection
- 2<sup>nd</sup> generation HighSpeed-Technology for 1200V applications offers:**
  - loss reduction in resonant circuits
  - temperature stable behavior
  - parallel switching capability
  - tight parameter distribution
  - $E_{off}$  optimized for  $I_C = 3A$
  - simple Gate-Control
- Qualified according to JEDEC<sup>1</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$E_{off}$	$T_{j,max}$	Marking	Package
IGA03N120H2	1200V	3A	0.15mJ	150°C	G03H1202	PG-TO-220-3-31
IGA03N120H2	1200V	3A	0.15mJ	150°C	G03H1202	PG-TO-220-3-34

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1200	V
Triangular collector peak current ( $V_{GS} = 15V$ ) $T_C = 100^\circ C, f = 32kHz$	$I_{Cpk}$	8.2	A
Pulsed collector current, $t_p$ limited by $T_{j,max}$	$I_{Cpuls}$	9	
Turn off safe operating area $V_{CE} \leq 1200V, T_j \leq 150^\circ C$	-	9	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Power dissipation $T_C = 25^\circ C$	$P_{tot}$	29	W
Operating junction and storage temperature	$T_j, T_{stg}$	-40...+150	°C
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	
Isolation Voltage	$V_{isol}$	2500	$V_{rms}$

<sup>1</sup> J-STD-020 and JESD-022

**Thermal Resistance**

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		4.3	KW
Thermal resistance, junction – ambient	$R_{thJA}$		64	

**Electrical Characteristic, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=300\mu A$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=3A$ $T_j=25\text{ }^\circ\text{C}$ $T_j=150\text{ }^\circ\text{C}$	-	2.2	2.8	
			-	2.5	-	
			-	2.4	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=90\mu A, V_{CE}=V_{GE}$	2.1	3	3.9	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25\text{ }^\circ\text{C}$ $T_j=150\text{ }^\circ\text{C}$	-	-	20	$\mu A$
			-	-	80	
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=3A$	-	2	-	S
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{iss}$	$V_{CE}=25V$	-	205	-	pF
Output capacitance	$C_{oss}$	$V_{GE}=0V$	-	24	-	
Reverse transfer capacitance	$C_{rss}$	$f=1\text{MHz}$	-	7	-	
Gate charge	$Q_{Gate}$	$V_{CC}=960V, I_C=3A$ $V_{GE}=15V$	-	8.6	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	7	-	nH

**Switching Characteristic, Inductive Load, at  $T_j=25^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$	-	9.2	-	ns
Rise time	$t_r$	$V_{CC}=800\text{V}, I_C=3\text{A}$	-	5.2	-	
Turn-off delay time	$t_{d(off)}$	$V_{GE}=0\text{V}/15\text{V}$	-	281	-	
Fall time	$t_f$	$R_G=82\Omega$	-	29	-	
Turn-on energy	$E_{on}$	$L_\sigma^{(2)}=180\text{nH}$	-	0.14	-	mJ
Turn-off energy	$E_{off}$	$C_\sigma^{(1)}=40\text{pF}$	-	0.15	-	
Total switching energy	$E_{ts}$	Energy losses include "tail" and diode <sup>2)</sup> reverse recovery.	-	0.29	-	

**Switching Characteristic, Inductive Load, at  $T_j=150^\circ\text{C}$** 

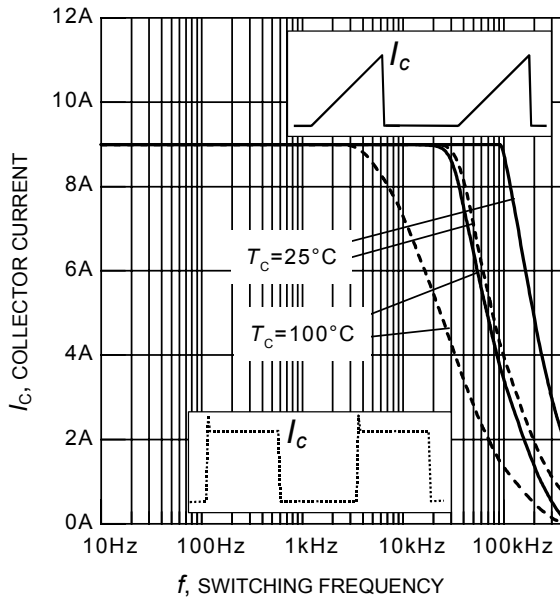
Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$	-	9.4	-	ns
Rise time	$t_r$	$V_{CC}=800\text{V}, I_C=3\text{A}$	-	6.7	-	
Turn-off delay time	$t_{d(off)}$	$V_{GE}=0\text{V}/15\text{V}$	-	340	-	
Fall time	$t_f$	$R_G=82\Omega$	-	63	-	
Turn-on energy	$E_{on}$	$L_\sigma^{(1)}=180\text{nH}$	-	0.22	-	mJ
Turn-off energy	$E_{off}$	$C_\sigma^{(1)}=40\text{pF}$	-	0.26	-	
Total switching energy	$E_{ts}$	Energy losses include "tail" and diode <sup>3)</sup> reverse recovery.	-	0.48	-	

**Switching Energy ZVT, Inductive Load**

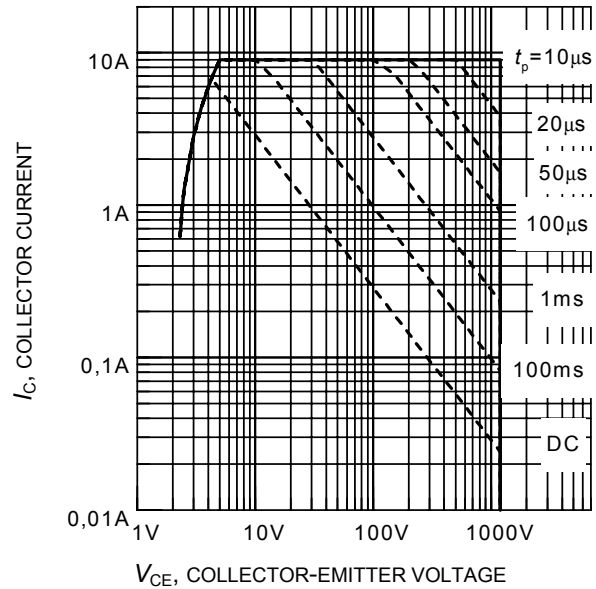
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-off energy	$E_{off}$	$V_{CC}=800\text{V}, I_C=3\text{A}$				mJ
		$V_{GE}=0\text{V}/15\text{V}$				
		$R_G=82\Omega, C_r^{(1)}=4\text{nF}$				
		$T_j=25^\circ\text{C}$	-	0.05	-	
		$T_j=150^\circ\text{C}$	-	0.09	-	

<sup>2)</sup> Leakage inductance  $L_\sigma$  and stray capacity  $C_\sigma$  due to dynamic test circuit in figure E

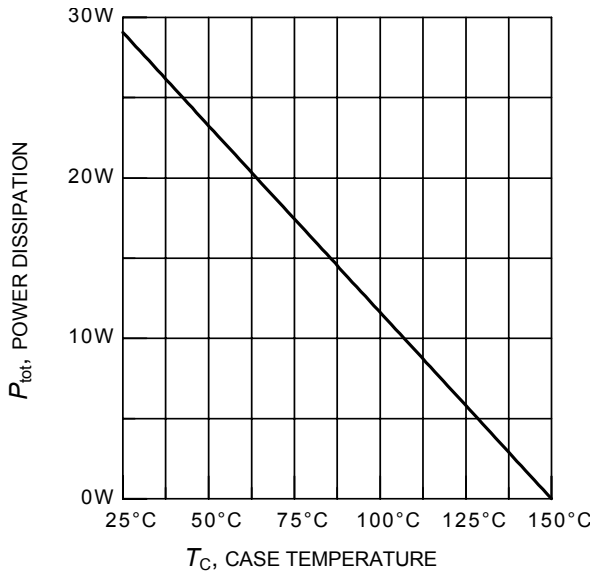
<sup>3)</sup> Commutation diode from device IKP03N120H2



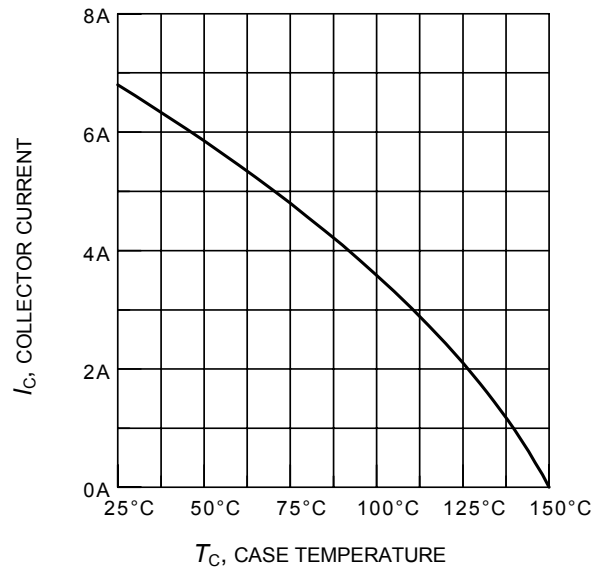
**Figure 1. Collector current as a function of switching frequency**  
 ( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 800\text{V}$ ,  
 $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 82\Omega$ )



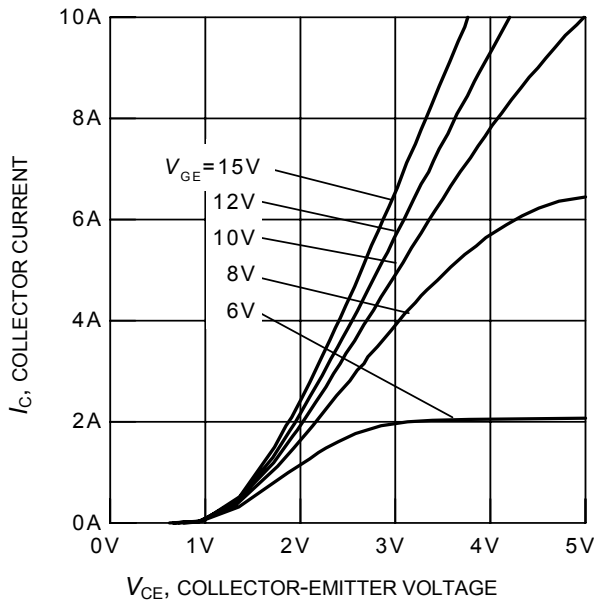
**Figure 2. Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 150^\circ\text{C}$ )



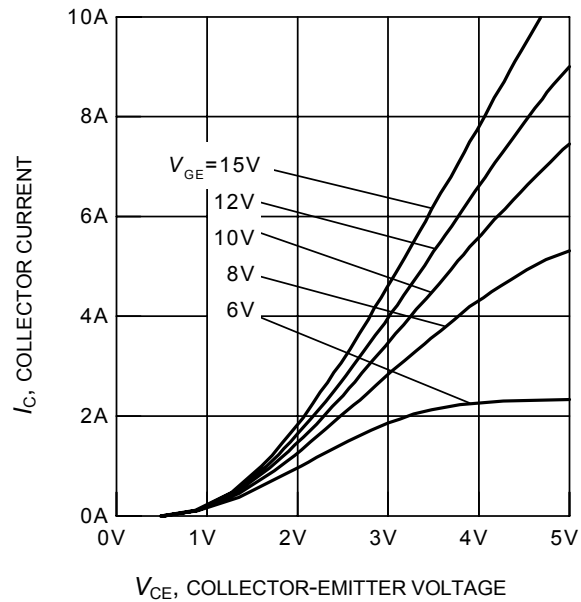
**Figure 3. Power dissipation as a function of case temperature**  
 ( $T_j \leq 150^\circ\text{C}$ )



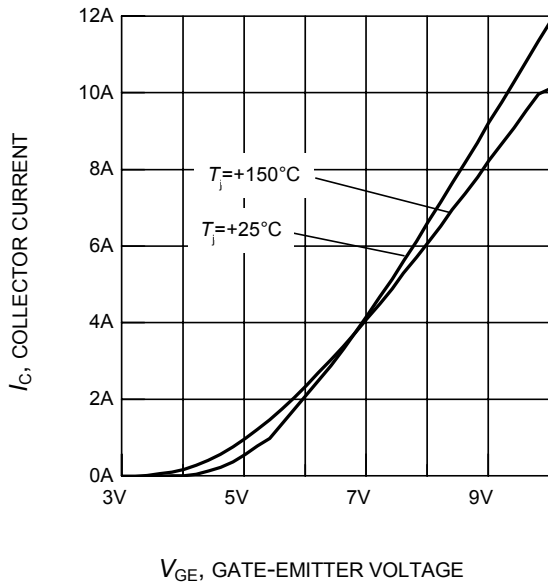
**Figure 4. Collector current as a function of case temperature**  
 ( $V_{GE} \leq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )



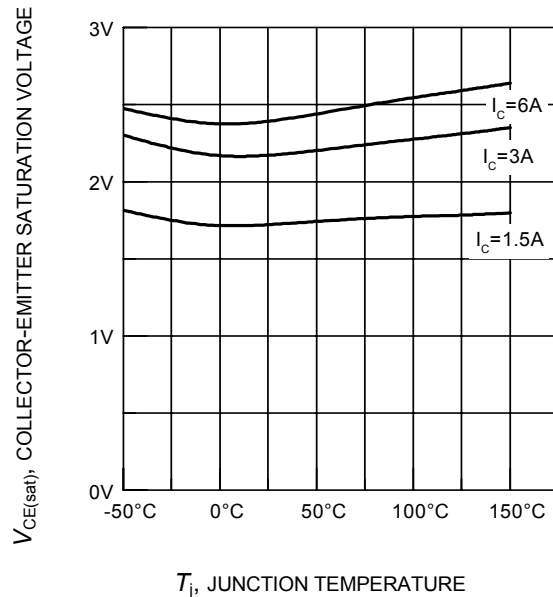
**Figure 5. Typical output characteristics**  
( $T_j = 25^\circ\text{C}$ )



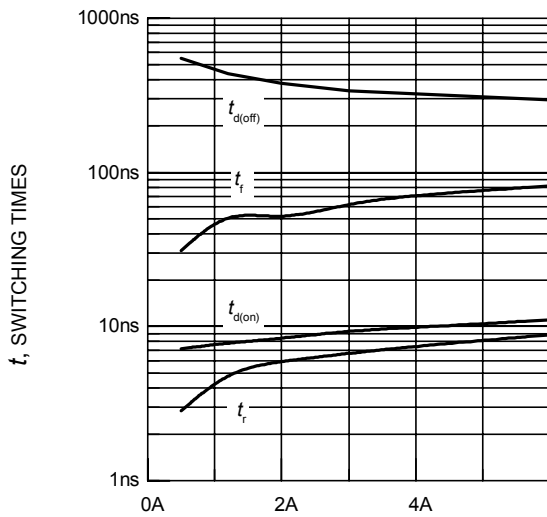
**Figure 6. Typical output characteristics**  
( $T_j = 150^\circ\text{C}$ )



**Figure 7. Typical transfer characteristics**  
( $V_{CE} = 20\text{V}$ )



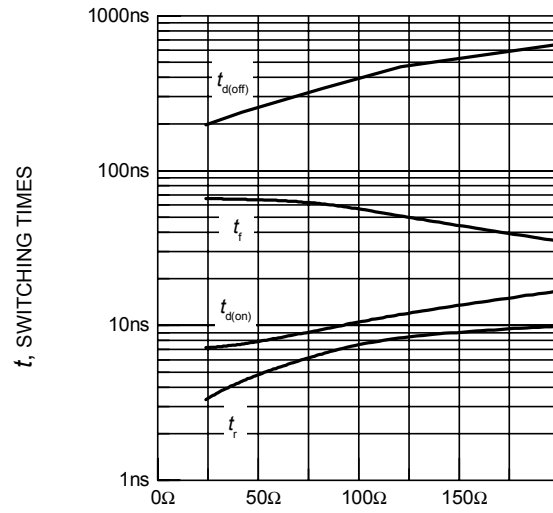
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



$I_C$ , COLLECTOR CURRENT

**Figure 9. Typical switching times as a function of collector current**

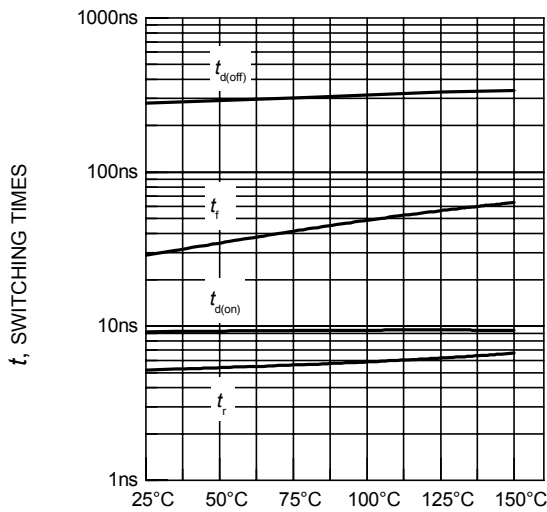
(inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 82\Omega$ , dynamic test circuit in Fig.E)



$R_G$ , GATE RESISTOR

**Figure 10. Typical switching times as a function of gate resistor**

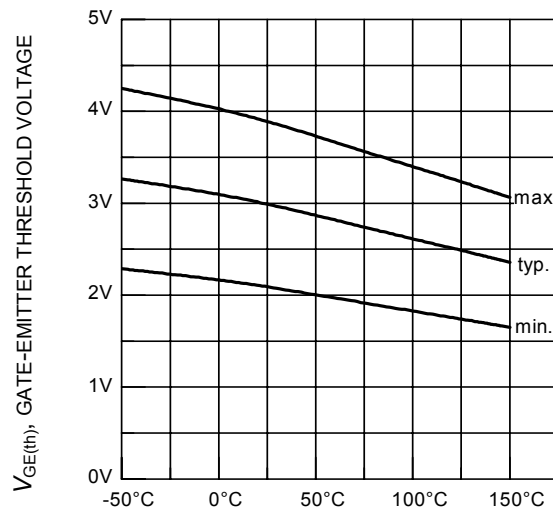
(inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 3\text{A}$ , dynamic test circuit in Fig.E)



$T_j$ , JUNCTION TEMPERATURE

**Figure 11. Typical switching times as a function of junction temperature**

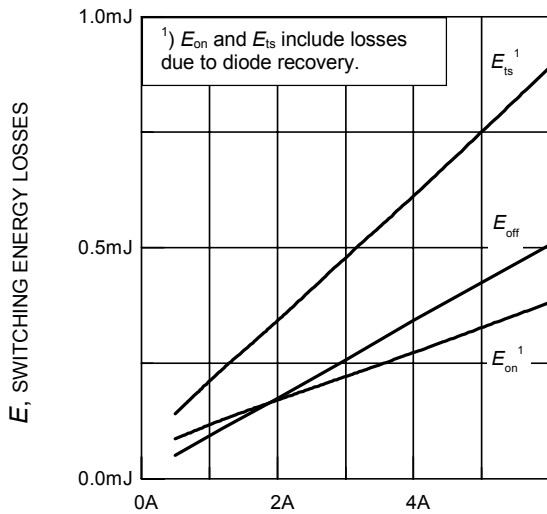
(inductive load,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 3\text{A}$ ,  $R_G = 82\Omega$ , dynamic test circuit in Fig.E)



$T_j$ , JUNCTION TEMPERATURE

**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**

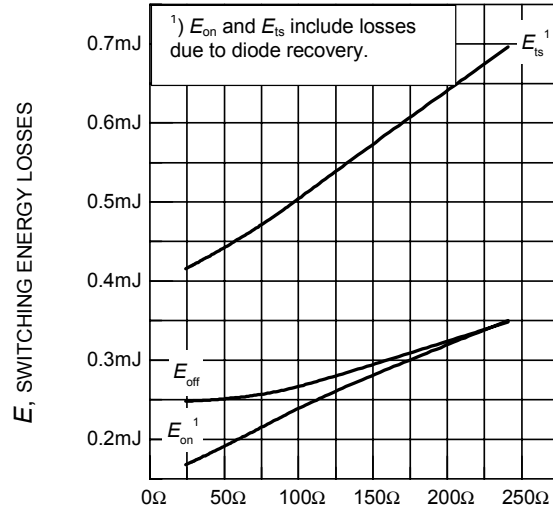
( $I_C = 0.09\text{mA}$ )



$I_C$ , COLLECTOR CURRENT

**Figure 13. Typical switching energy losses as a function of collector current**

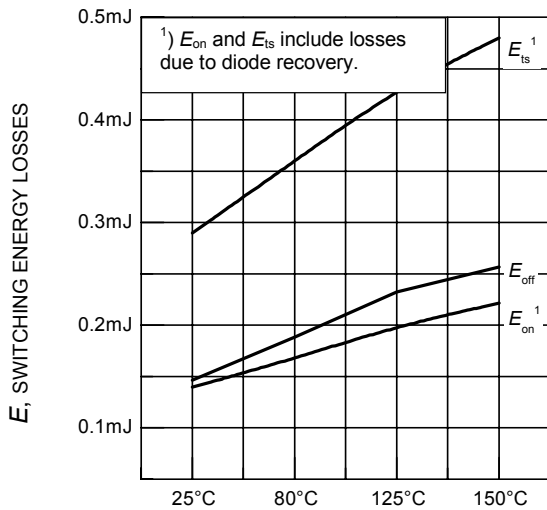
(inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 82\Omega$ , dynamic test circuit in Fig.E )



$R_G$ , GATE RESISTOR

**Figure 14. Typical switching energy losses as a function of gate resistor**

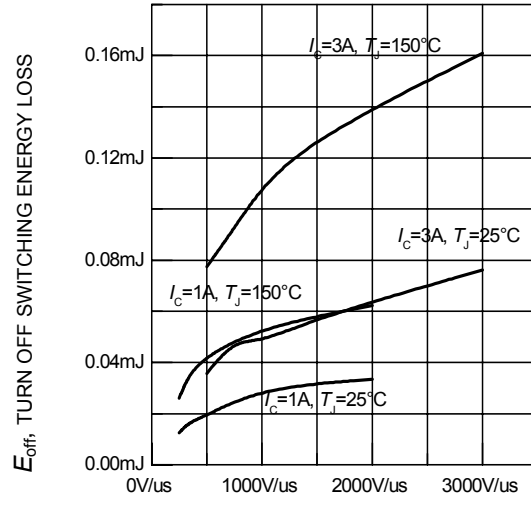
(inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 3\text{A}$ , dynamic test circuit in Fig.E )



$T_j$ , JUNCTION TEMPERATURE

**Figure 15. Typical switching energy losses as a function of junction temperature**

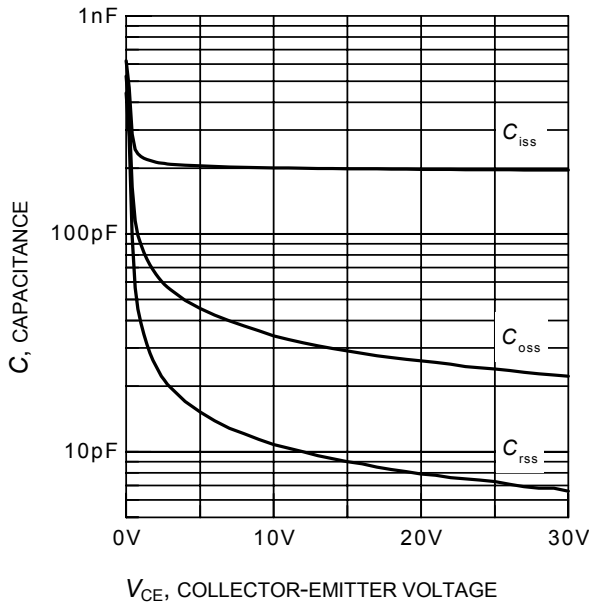
(inductive load,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 3\text{A}$ ,  $R_G = 82\Omega$ , dynamic test circuit in Fig.E )



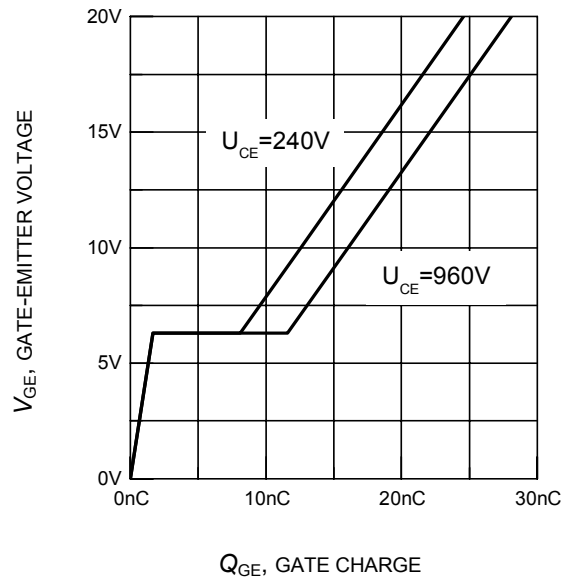
$dv/dt$ , VOLTAGE SLOPE

**Figure 16. Typical turn off switching energy loss for soft switching**

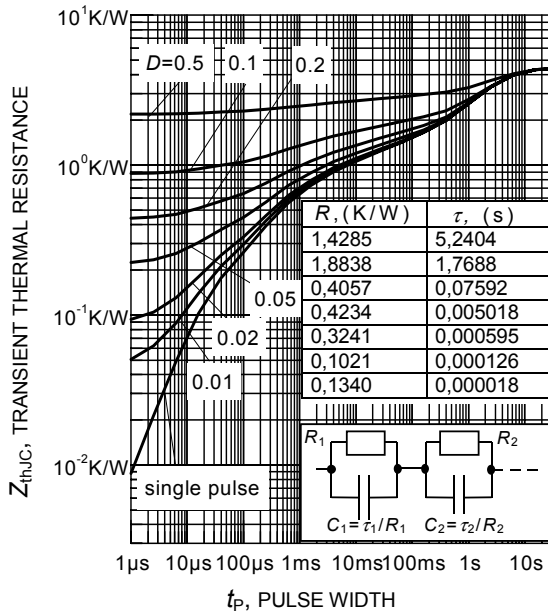
(dynamic test circuit in Fig. E)



$V_{CE}$ , COLLECTOR-EMITTER VOLTAGE  
**Figure 19. Typical capacitance as a function of collector-emitter voltage**  
 ( $V_{GE} = 0V, f = 1MHz$ )



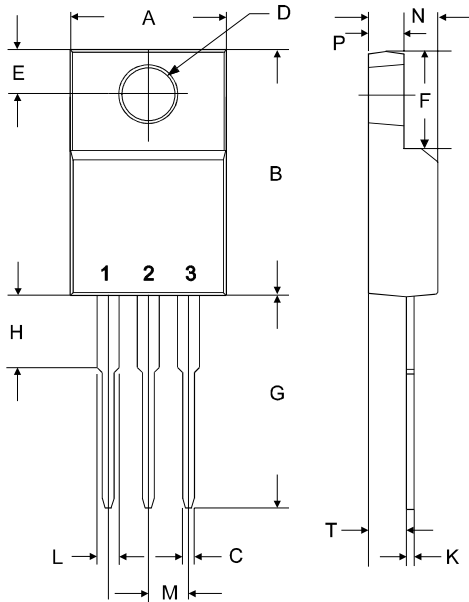
$Q_{GE}$ , GATE CHARGE  
**Figure 18. Typical gate charge**  
 ( $I_C = 3A$ )



**Figure 17. IGBT transient thermal impedance as a function of pulse width**  
 ( $D=t_p/T$ )



PG-TO-220-3-31 (FullPAK)



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	10.37	10.63	0.4084	0.4184
B	15.86	16.12	0.6245	0.6345
C	0.65	0.78	0.0256	0.0306
D	2.95 typ.		0.1160 typ.	
E	3.15	3.25	0.124	0.128
F	6.05	6.56	0.2384	0.2584
G	13.47	13.73	0.5304	0.5404
H	3.18	3.43	0.125	0.135
K	0.45	0.63	0.0177	0.0247
L	1.23	1.36	0.0484	0.0534
M	2.54 typ.		0.100 typ.	
N	4.57	4.83	0.1800	0.1900
P	2.57	2.83	0.1013	0.1113
T	2.51	2.62	0.0990	0.1030

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